L Number	Hits	Search Text	DB	Time stamp
1	102	((438/3,253,254,238,239,396).CCLS.) and buried near3 contact and	USPAT;	2004/07/22 10:26
		ferroelectric and contact adj hole	US-PGPUB;	
			ЕРО; ЛРО;	
			DERWENT;	
			IBM TDB	
2	5586	ferroelectric adj memory	USPAT;	2004/07/22 10:26
	5500	101100100 and internet	US-PGPUB;	
			ЕРО; ЛРО;	
			DERWENT;	
			IBM_TDB	
3	41	(((438/3,253,254,238,239,396).CCLS.) and buried near3 contact and ferroelectric and contact adj hole) and (ferroelectric adj memory)	USPAT;	2004/07/22 10:27
			US-PGPUB;	2004/07/22 10.27
1		Terroelectric and contact adj noicy and (terroelectric adj inemoly)	EPO; JPO;	
			DERWENT;	
.	1	(/057/005 000 010 500) COV (I) 1 (I) 1 (II)	IBM_TDB	2004/05/02 10 51
4	1	((257/295,298,310,532).CCLS.) and (insulat\$3 and substrate and contact adj hole and (burry or burried))	USPAT;	2004/07/22 10:51
			US-PGPUB;	
			ЕРО; ЈРО;	
			DERWENT;	
	78	((((257/295,298,310,532).CCLS.) and buried near3 contact) and ferroelectric) and contact adj hole	IBM_TDB	
5			USPAT;	2004/07/22 10:53
			US-PGPUB;	
			ЕРО; ЈРО;	
			DERWENT;	
			IBM_TDB	
6	273	buried near3 contact and ferroelectric and contact adj hole	USPAT;	2004/07/22 10:54
			US-PGPUB;	
			ЕРО; ЈРО;	
			DERWENT;	
			IBM_TDB	
7	15	buried near3 (contact near3 structure) and ferroelectric and contact adj	USPAT;	2004/07/22 10:54
		hole	US-PGPUB;	
			ЕРО; ЈРО;	
			DERWENT;	
	46	insulat\$3 and substrate and contact adj hole and (burry or burried)	IBM_TDB	
8			USPAT;	2004/07/22 10:58
			US-PGPUB;	
			ЕРО; ЈРО;	
			DERWENT;	
			IBM TDB	
9	0	(ferroelectric adj memory) and (insulat\$3 and substrate and contact adj hole and (burry or burried))	USPĀT;	2004/07/22 10:58
			US-PGPUB;	
			ЕРО; ЛРО;	
			DERWENT;	
			IBM_TDB	
10	3088	(((blocking adj layer) (etch adj stop)) near9 ((silicon adj nitride) (silicon	USPAT;	2004/07/22 11:03
	3000	adj oxinitride) "SiOn" SiN))	US-PGPUB;	
		aug (Aminarae) Sion Sh'y)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
11	46	(((silicon adj oxynitride) "SiON") or ((silicon adj nitride) "SiN")) and	USPAT;	2004/07/22 11:01
* 1	4 0	((((257/295,298,310,532).CCLS.) and buried near3 contact) and	US-PGPUB;	2004/0//22 11.01
1		ferroelectric and plug with (tungsten 'W')		
		remoercoure and plug with (thingsten w)	EPO; JPO;	
i			DERWENT;	
12	750	((((blocking adj layer) (etch adj stop)) near9 ((silicon adj nitride)	IBM_TDB	2004/07/22 11 22
			USPAT;	2004/07/22 11:02
ļ		(silicon adj oxinitride) (aluminum adj oxide) "SiOn" "SiN" "AlO"))) and	US-PGPUB;	
İ		dram	ЕРО; ЈРО;	
			DERWENT;	
			IBM_TDB	

13	49	(ferroelectric adj memory) and (((((blocking adj layer) (etch adj stop))	USPAT;	2004/07/22 11:02
ŀ		near9 ((silicon adj nitride) (silicon adj oxinitride) (aluminum adj oxide)	US-PGPUB;	
		"SiOn" "SiN" "AlO"))) and dram)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
14	53	(ferroelectric adj memory) and ((((blocking adj layer) (etch adj stop))	USPAT;	2004/07/22 11:03
l		near9 ((silicon adj nitride) (silicon adj oxinitride) "SiOn" SiN)))	US-PGPUB;	
			ЕРО; ЛРО;	
1			DERWENT;	
			IBM_TDB	